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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



UP03312

Silicon NPN epitaxial planar type (Tr1)
 Silicon PNP epitaxial planar type (Tr2)

For digital circuits

■ Features

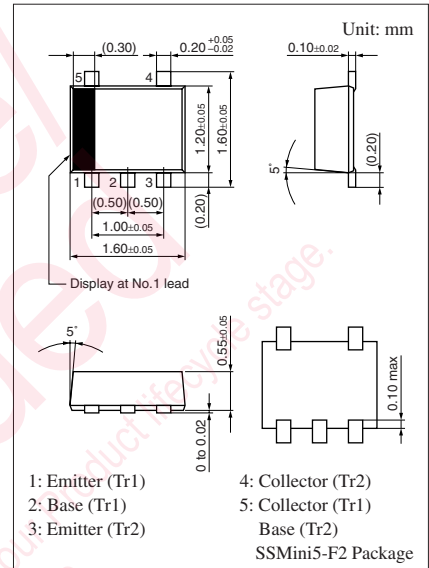
- Two elements incorporated into one package
 (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

■ Basic Part Number

- UNR1112 + UNR1212

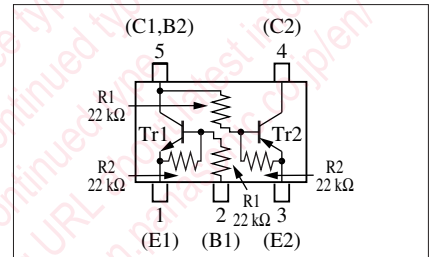
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| | Parameter | Symbol | Rating | Unit |
|---------|--|------------------|-------------|------------------|
| Tr1 | Collector-base voltage (Emitter open) | V_{CBO} | 50 | V |
| | Collector-emitter voltage (Base open) | V_{CEO} | 50 | V |
| | Collector current | I_{C} | 100 | mA |
| Tr2 | Collector-base voltage (Emitter open) | V_{CBO} | -50 | V |
| | Collector-emitter voltage (Base open) | V_{CEO} | -50 | V |
| | Collector current | I_{C} | -100 | mA |
| Overall | Total power dissipation | P_{T} | 125 | mW |
| | Junction temperature | T_{j} | 125 | $^\circ\text{C}$ |
| | Storage temperature | T_{stg} | -55 to +125 | $^\circ\text{C}$ |



Marking Symbol: 4P

Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr1

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|-------------------------------|---|------|-----|------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_{\text{C}} = 10 \mu\text{A}, I_{\text{E}} = 0$ | 50 | | | V |
| Collector-emitter voltage (Base open) | V_{CEO} | $I_{\text{C}} = 2 \text{ mA}, I_{\text{B}} = 0$ | 50 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{\text{CB}} = 50 \text{ V}, I_{\text{E}} = 0$ | | | 0.1 | μA |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{\text{CE}} = 50 \text{ V}, I_{\text{B}} = 0$ | | | 0.5 | μA |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{\text{EB}} = 6 \text{ V}, I_{\text{C}} = 0$ | | | 0.2 | mA |
| Forward current transfer ratio | h_{FE} | $V_{\text{CE}} = 10 \text{ V}, I_{\text{C}} = 5 \text{ mA}$ | 60 | | | — |
| Collector-emitter saturation voltage | $V_{\text{CE(sat)}}$ | $I_{\text{C}} = 10 \text{ mA}, I_{\text{B}} = 0.3 \text{ mA}$ | | | 0.25 | V |
| Output voltage high-level | V_{OH} | $V_{\text{CC}} = 5 \text{ V}, V_{\text{B}} = 0.5 \text{ V}, R_{\text{L}} = 1 \text{ k}\Omega$ | 4.9 | | | V |
| Output voltage low-level | V_{OL} | $V_{\text{CC}} = 5 \text{ V}, V_{\text{B}} = 2.5 \text{ V}, R_{\text{L}} = 1 \text{ k}\Omega$ | | | 0.2 | V |
| Input resistance | R_{I} | | -30% | 22 | +30% | $\text{k}\Omega$ |
| Resistance ratio | $R_{\text{I}} / R_{\text{2}}$ | | 0.8 | 1.0 | 1.2 | — |
| Transition frequency | f_{T} | $V_{\text{CB}} = 10 \text{ V}, I_{\text{E}} = -2 \text{ mA}, f = 200 \text{ MHz}$ | | 150 | | MHz |

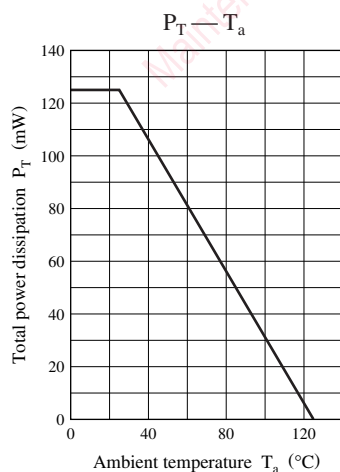
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

• Tr2

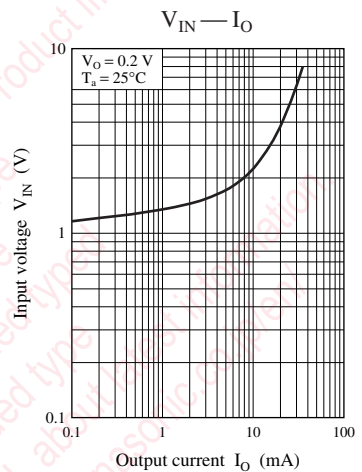
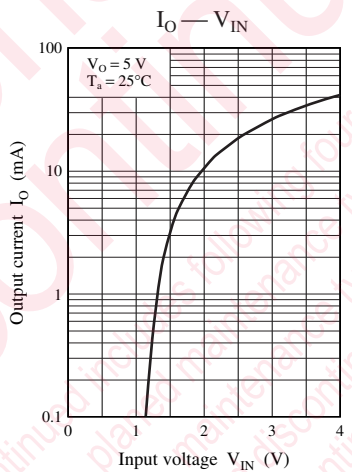
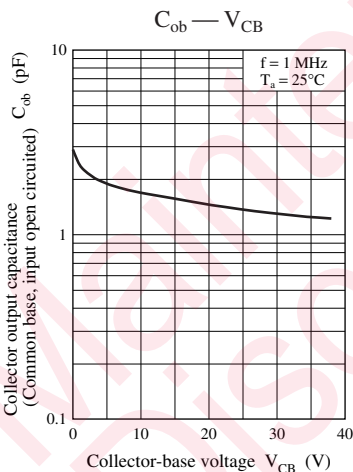
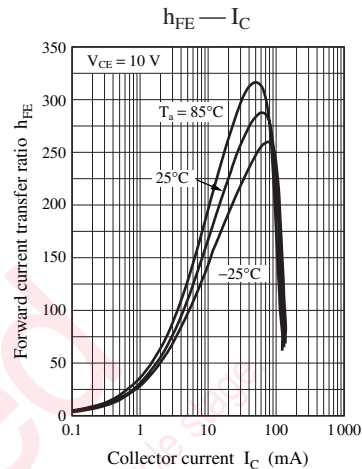
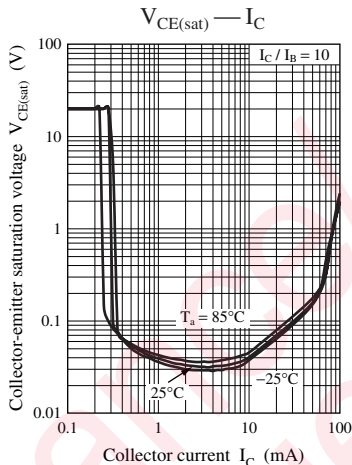
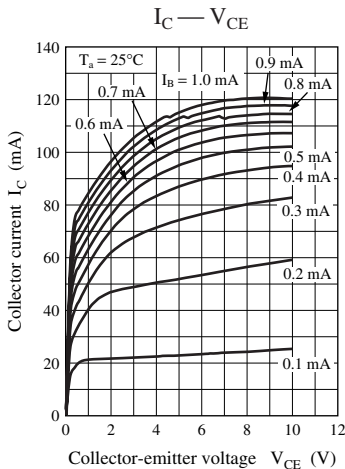
| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|-------------------------------|---|------|-----|-------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_{\text{C}} = -10 \mu\text{A}, I_{\text{E}} = 0$ | -50 | | | V |
| Collector-emitter voltage (Base open) | V_{CEO} | $I_{\text{C}} = -2 \text{ mA}, I_{\text{B}} = 0$ | -50 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{\text{CB}} = -50 \text{ V}, I_{\text{E}} = 0$ | | | -0.1 | μA |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{\text{CE}} = -50 \text{ V}, I_{\text{B}} = 0$ | | | -0.5 | μA |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{\text{EB}} = -6 \text{ V}, I_{\text{C}} = 0$ | | | -0.2 | mA |
| Forward current transfer ratio | h_{FE} | $V_{\text{CE}} = -10 \text{ V}, I_{\text{C}} = -5 \text{ mA}$ | 60 | | | — |
| Collector-emitter saturation voltage | $V_{\text{CE(sat)}}$ | $I_{\text{C}} = -10 \text{ mA}, I_{\text{B}} = -0.3 \text{ mA}$ | | | -0.25 | V |
| Output voltage high-level | V_{OH} | $V_{\text{CC}} = -5 \text{ V}, V_{\text{B}} = -0.5 \text{ V}, R_{\text{L}} = 1 \text{ k}\Omega$ | -4.9 | | | V |
| Output voltage low-level | V_{OL} | $V_{\text{CC}} = -5 \text{ V}, V_{\text{B}} = -2.5 \text{ V}, R_{\text{L}} = 1 \text{ k}\Omega$ | | | -0.2 | V |
| Input resistance | R_{I} | | -30% | 22 | +30% | $\text{k}\Omega$ |
| Resistance ratio | $R_{\text{I}} / R_{\text{2}}$ | | 0.8 | 1.0 | 1.2 | — |
| Transition frequency | f_{T} | $V_{\text{CB}} = -10 \text{ V}, I_{\text{E}} = 1 \text{ mA}, f = 200 \text{ MHz}$ | | 80 | | MHz |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

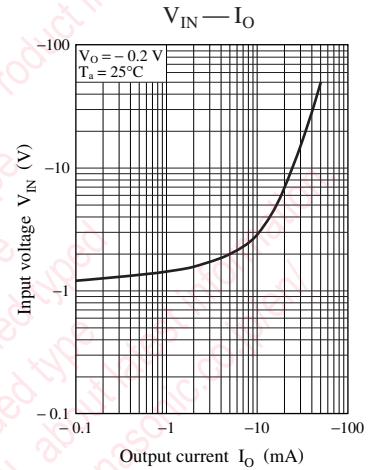
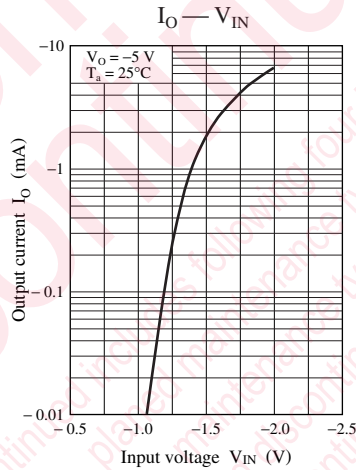
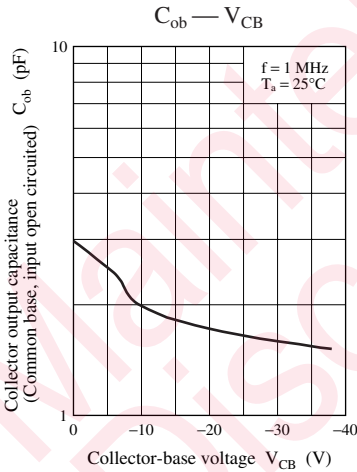
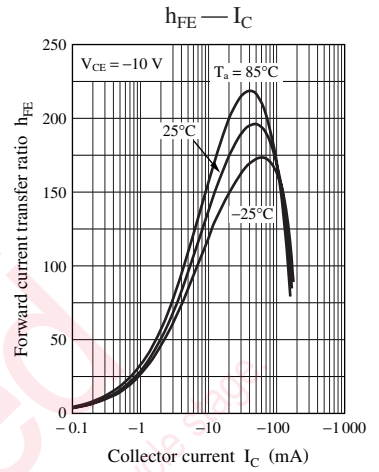
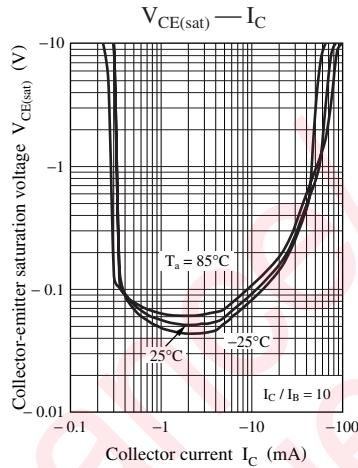
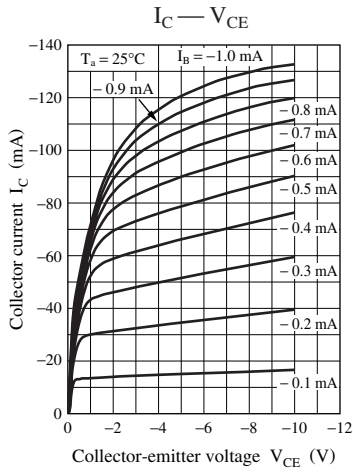
Common characteristics chart



Characteristics charts of Tr1



Characteristics charts of Tr2



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